

APPENDIX

Shown below is a copy of the claims involved in the appeal, as the applicants understand them to stand.

9. A flash memory comprising:
 - a semiconductor substrate that includes a flash memory cell that has a floating gate;
 - a conductive layer formed on the substrate; and
 - a passivation layer formed on the conductive layer that is not transparent to ultraviolet light, the passivation layer covering the flash memory cell.
10. The flash memory of claim 9 wherein the passivation layer comprises a barrier layer and a stress reduction layer.
11. The flash memory of claim 10 wherein the passivation layer comprises a silicon nitride layer and a polyimide layer.
12. The flash memory of claim 11 wherein the flash memory cell's floating gate has a gate length that is less than about 0.5 microns.
13. The flash memory of claim 12 wherein the conductive layer forms the final metal interconnect for the flash memory, upon which is formed the passivation layer.
14. The flash memory of claim 13 wherein the silicon nitride layer is between about 2,000 and about 10,000 angstroms thick.
15. The flash memory of claim 9 wherein the passivation layer comprises a polyimide layer.